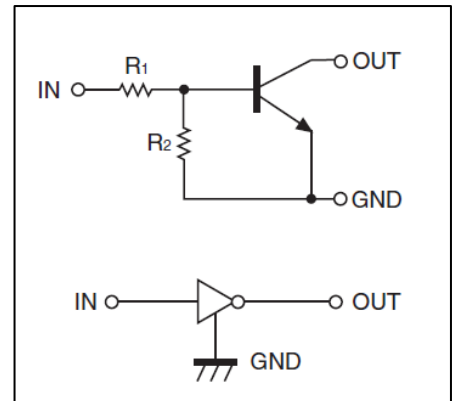


## NPN Silicon Epitaxial Planar Digital Transistor

### FEATURES

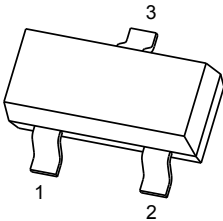
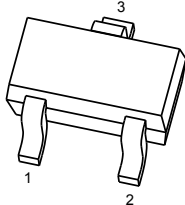
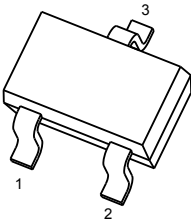
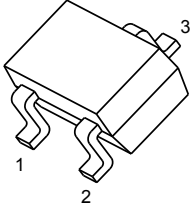
- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors(see equivalent circuit)
- The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input.They also have the advantage of almost completely eliminating parasitic effects
- Only the on/off conditions need to be set for operation, making device designs easy

### Equivalent Circuit



### MARKING: 24

### PIN CONNENCTIONS and MARKING

<p><b>DTC114ECA</b></p>  <p>1. IN 2. GND 3. OUT</p>	<p><b>DTC114EE</b></p>  <p>1. IN 2. GND 3. OUT</p>
<p><b>DTC114EUA</b></p>  <p>1. IN 2. GND 3. OUT</p>	<p><b>DTC114EKA</b></p>  <p>1. IN 2. GND 3. OUT</p>

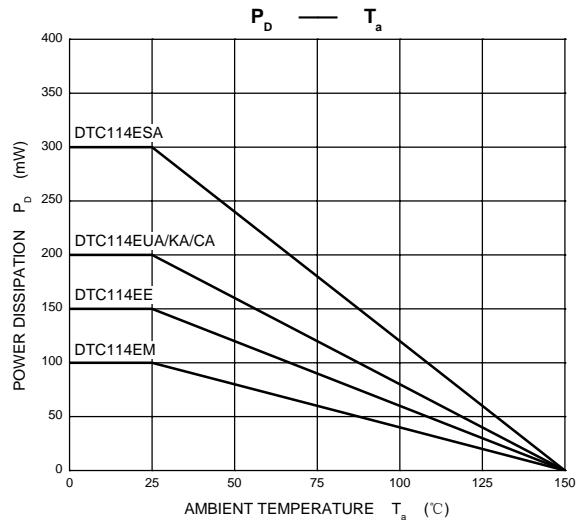
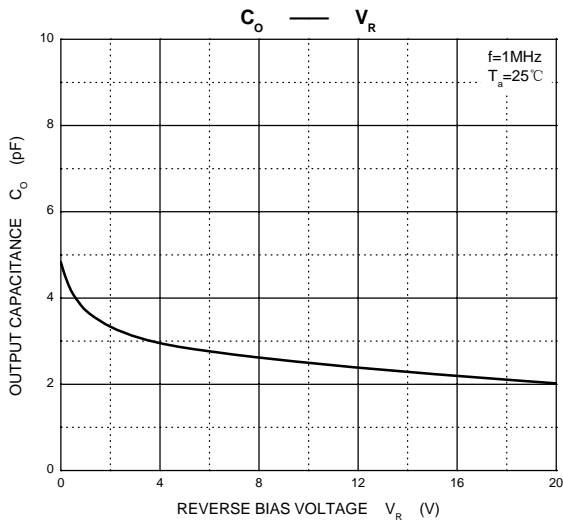
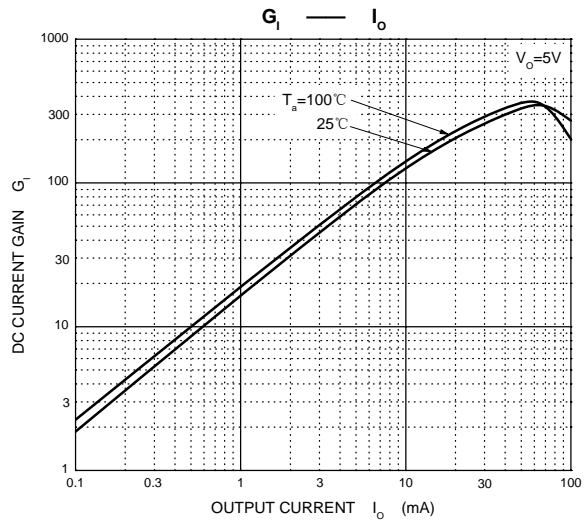
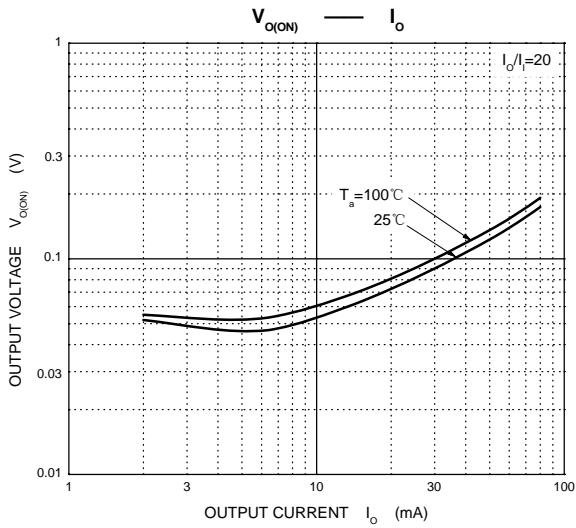
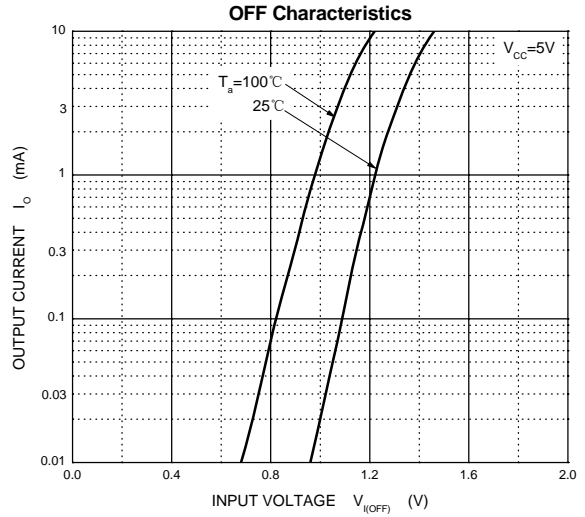
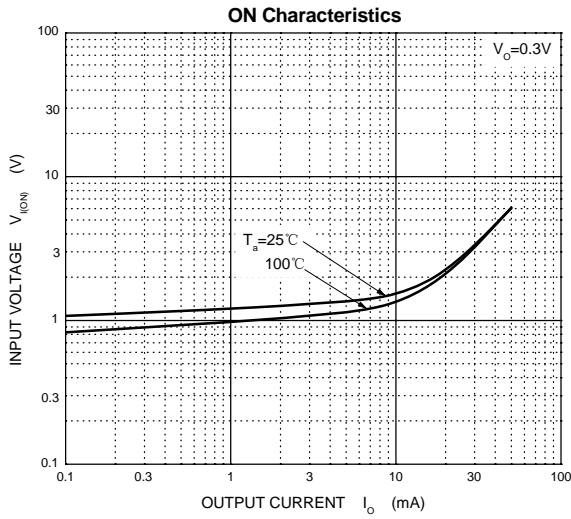
**MAXIMUM RATINGS(Ta=25°C unless otherwise noted)**

Symbol	Parameter	Limits(DTC114E□)					Unit
			E	UA	CA	KA	
V <sub>CC</sub>	Supply Voltage	50					V
V <sub>IN</sub>	Input Voltage	-10~+40					V
I <sub>O</sub>	Output Current	50					mA
I <sub>CM</sub>	Peak Collector Current	100					mA
P <sub>D</sub>	Power Dissipation		150	200	200	200	mW
T <sub>J</sub>	Junction Temperature	150					°C
T <sub>stg</sub>	Storage Temperature	-55~+150					°C

**ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)**

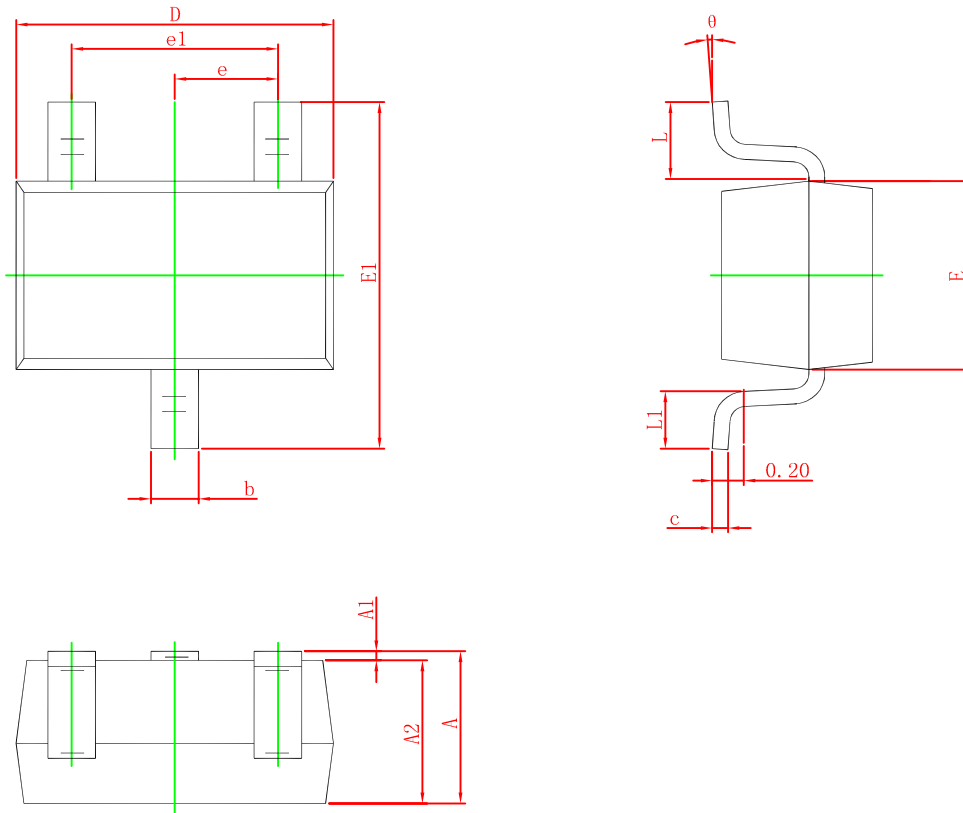
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Input voltage	V <sub>I(off)</sub>	V <sub>CC</sub> =5V, I <sub>O</sub> =100μA	0.5			V
	V <sub>I(on)</sub>	V <sub>O</sub> =0.3V, I <sub>O</sub> =10mA			3	V
Output voltage	V <sub>O(on)</sub>	I <sub>O</sub> /I <sub>I</sub> =10mA/0.5mA			0.3	V
Input current	I <sub>I</sub>	V <sub>I</sub> =5V			0.88	mA
Output current	I <sub>O(off)</sub>	V <sub>CC</sub> =50V, V <sub>I</sub> =0			0.5	μA
DC current gain	G <sub>I</sub>	V <sub>O</sub> =5V, I <sub>O</sub> =5mA	30			
Input resistance	R <sub>1</sub>		7	10	13	kΩ
Resistance ratio	R <sub>2</sub> /R <sub>1</sub>		0.8	1	1.2	
Transition frequency	f <sub>T</sub>	V <sub>O</sub> =10V, I <sub>O</sub> =5mA, f=100MHz		250		MHz

## TYPICAL CHARACTERISTICS



PACKAGE OUTLINE

SOT-323



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP.		0.026 TYP.	
e1	1.200	1.400	0.047	0.055
L	0.525 REF.		0.021 REF.	
L1	0.260	0.460	0.010	0.018
$\theta$	0°	8°	0°	8°

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[DTC115TKAT146](#) [DTC124TETL](#) [DTC144VUAT106](#) [MUN5241T1G](#) [BCR158WH6327XTSA1](#) [NSBA114TDP6T5G](#) [NSBA123EF3T5G](#)  
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